

						d(A)	Int	h	k	l					
Ce4.667(SiO4)30						d(A)	Int	h	k	l	d(A)	Int	h	k	l
Cerium Oxide Silicate						4.8257	4	1	1	0	1.7798	11	0	0	4
						4.1801	30	2	0	0	1.6870	2	3	2	2
						3.9948	24	1	1	1	1.6360	4	2	0	4
						3.5589	16	0	0	2	1.6246	2	4	1	2
Rad: CuK α 1 λ : 1.5406 Filter: Mono d-sp: Guinier 57.16						3.2751	37	1	0	2	1.5804	5	4	2	0
Cut off: 17.7 Int.: I/Incor.:						3.1611	42	2	1	0	1.5700	9	3	3	1
Ref: Tas, A., Akinc, M., Powder Diffraction, 7, 219 (1992)						2.8895	100	2	1	1	1.5509	10	2	1	4
						2.8655	53	1	1	2	1.5435	2	4	2	1
						2.7885	34	3	0	0	1.5138	13	5	0	2
						2.7109	3	2	0	2	1.5016	2	5	1	0
Sys: Hexagonal S.G.: P6 $_3$ /m (176)						2.3196	7	3	1	0	1.5002	5	3	0	4
a: 9.6578(4) b: c: 7.1187(4) A: C: 0.7371						2.2865	4	2	2	1	1.4920	8	3	2	3
α : β : γ : Z: 2 mp:						2.2058	3	3	1	1	1.4697	7	5	1	1
Ref: Ibid.						2.1952	5	3	0	2	1.4666	9	3	3	2
						2.1297	10	1	1	3	1.4468	2	4	1	3
Dx: 5.465 Dm: SS/FOM: F $_{30}$ = 67(.0092 , 49)						2.0912	6	4	0	0	1.3839	2	5	1	2
						2.0635	1	2	0	3	1.3750	4	4	3	0
						1.9983	31	2	2	2	1.3555	3	4	0	4
						1.9434	16	3	1	2	1.3503	2	4	3	1
						1.8980	38	2	1	3	1.3390	2	5	2	0
						1.8528	19	3	2	1	1.3320	4	3	3	3
						1.8253	29	4	1	0	1.3162	8	5	2	1
Silicon used as an internal stand. PSC: hP41.33. To replace						1.8029	32	4	0	2	1.3050	3	3	2	4
31-336. Mwt: 946.19. Volume[CD]: 575.03.															

d(A)	Int	h	k	l
1.2980	11	6	0	2
1.2744	22	4	1	4
1.2692	3	5	1	3
1.2552	8	6	1	1
1.2534	14	5	2	2
1.2261	1	2	2	5
1.2189	2	5	0	4
1.2071	3	4	4	0
1.1820	6	0	0	6
1.1820		4	2	4
1.1743	2	1	0	6
1.1517	4	1	1	6